# **MSKSEMI**美森科













ESD

TVS

TSS

MOV

GDT

PLED



**Product specification** 





### Features

- 150Watts peak pulse power (tp = 8/20µs)
- Transient protection for high speed data lines to IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
  IEC 61000-4-4 (EFT) 40A (5/50ns)
- Working voltages : 5V
- Protects fivel/O lines
- Low operatingand clamping voltages
- Solid-state silicon avalanche technology

## Applications

- Notebooks, Desktops, Servers and Video Graphics Cards
- USB Power & Data Line Protection
- Monitors and Flat Panel Displays
- I<sup>2</sup>C Bus Protection
- Portable Instrumentation
- Set Top Box

### **Reference News**

Outline	Circuit Diagram	Marking	
		•M534	
DFN2010-5L	2		

#### Maximum Rating @ Ta=25°Cunless otherwise specified

Symbol	Parameter	Ratings	Units
Ррк	Peak Pulse Power (tp = 8/20µs)	150	Watts
Τι	Lead Soldering Temperature	260(10sec.)	°C
TJ	Operating Temperature	-55 to +125	°C
Тѕтс	Storage Temperature	-55 to +150	°C

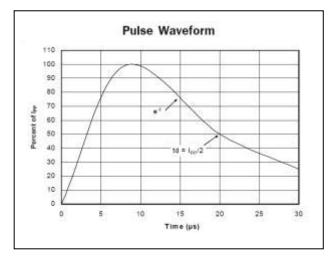


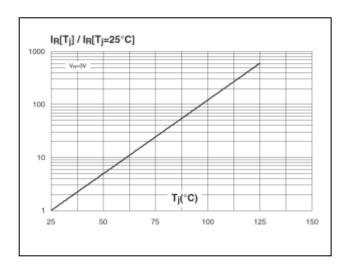
# ElectricalCharacteristics@ Ta=25℃ unless otherwise

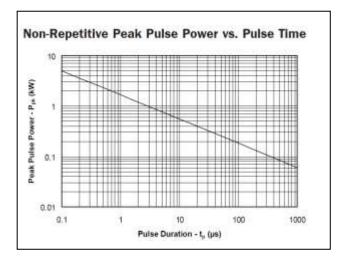
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Vrwm	Reverse Working Voltage	Any I/O to Ground			5.0	V
Vbr	Reverse Breakdown Voltage	ரி = 1mA, Any I/O to Ground	6.0			V
<b>I</b> R	Reverse Leakage Current	V <sub>RWM</sub> = 5V, Any I/O to Ground			1	μA
V <sub>c</sub> Cla	Clamping Voltage	I <sub>PP</sub> =  1A, tp  =8/20µs, any  I/O pin to Ground			9.8	V
VC		I <sub>PP</sub> = 3.5A, tp =8/20µs, any I/O pin to Ground			15	V
CJ	Junction Capacitance	V <sub>R</sub> = 0V, f = 1MHz, between I/O pins		0.3	0.5	pF
		V <sub>R</sub> = 0V, f = 1MHz, any I/O pin to Ground		0.5	0.8	pF

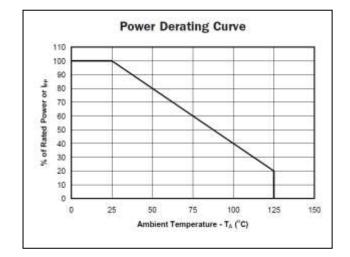


# Typical Characteristics@ Ta=25°C unless otherwise specified





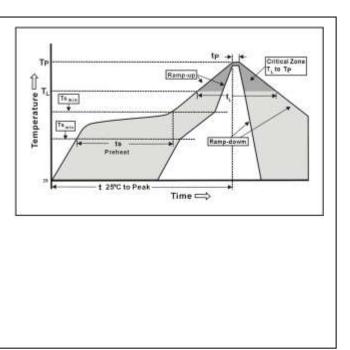






# **Soldering Parameters**

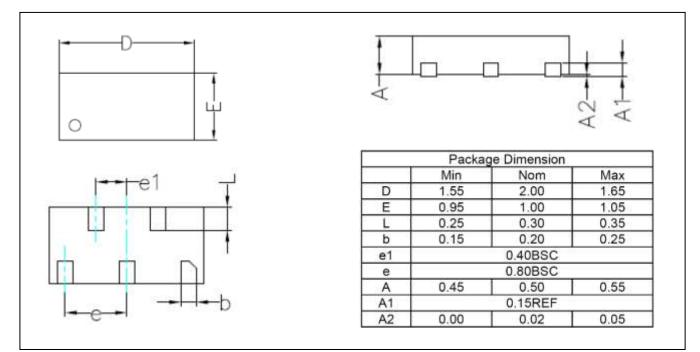
Reflow Co	ondition	Fb – Free assembly
	-Temperature Min (T <sub>s(Min)</sub> )	150°C
Pre Heat	- Temperature Max (T <sub>s(Max)</sub> )	200°C
	-Time (Min to max) (t_)	60 - 180 secs
Average r (T <sub>.</sub> ) to pea	amp up rate (Liquidus) Temp Ik	3°C/second Max
T <sub>s (Max)</sub> to T	- Ramp-up Rate	3°C/second Max
Reflow	-Temperature (T <sub>1</sub> ) (Liquidus)	217°C
Kellow	-Temperature (t <sub>i</sub> )	60 – 150 seconds
Peak Tem	perature (T,)	250*0-5 °C
Time with Temperat	in 5°C of actual peak ure (t <sub>r</sub> )	20 – 40 seconds
Ramp-dov	vm Rate	6°C/second Max
Time 25°C to peak Temperature (T <sub>p</sub> )		8 minutes Max.
Do not ex	ceed	260°C



# Package Outline

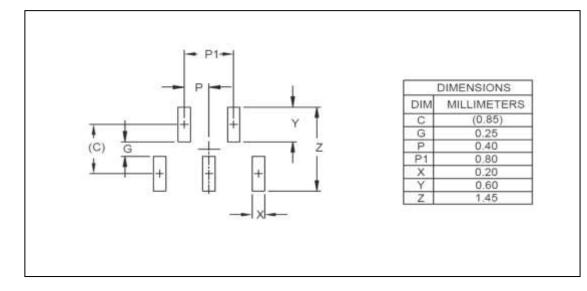
#### Plastic surface mounted package

#### DFN2010-5L





# Soldering Footprint



## **REEL SPECIFICATION**

P/N	PKG	QTY
RCLAMP7534P-MS	DFN2010-5L	3000



#### Attention

Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.

Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuits for safedesign, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or

mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements intellectual property rights or other rights of third parties.

Any and all information described or contained herein are subject to change without notice due to

product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.